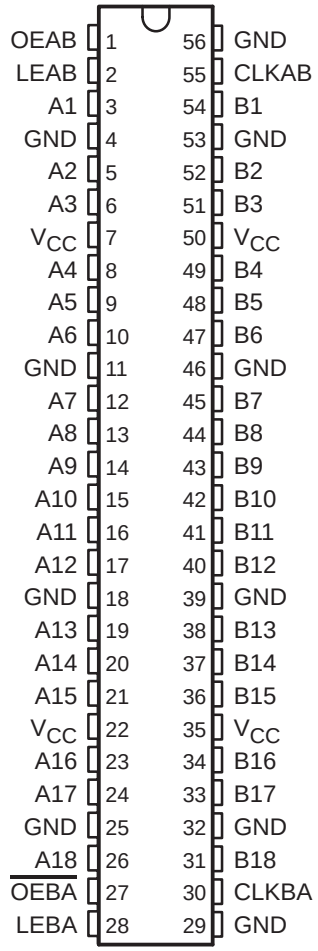
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, Clocked, or Clock-Enabled Mode**
- **State-of-the-Art Advanced BiCMOS Technology (ABT) *Widebus*™ Design for 2.5-V and 3.3-V Operation and Low Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 2.3-V to 3.6-V V_{CC})**
- **Typical V_{OLP} (Output Ground Bounce) <0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **High Drive (–24/24 mA at 2.5-V and –32/64 mA at 3.3-V V_{CC})**
- **Power Off Disables Outputs, Permitting Live Insertion**
- **High-Impedance State During Power Up and Power Down Prevents Driver Conflict**
- **Use Bus Hold on Data Inputs in Place of External Pullup/Pulldown Resistors to Prevent the Bus From Floating**
- **Auto3-State Eliminates Bus Current Loading When Output Exceeds V_{CC} + 0.5 V**
- **Flow-Through Architecture Facilitates Printed Circuit Board Layout**
- **Distributed V_{CC} and GND Pin Configuration Minimizes High-Speed Switching Noise**
- **Package Options Include Plastic Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), Thin Very Small-Outline (DGV) Packages, and 380-mil Fine-Pitch Ceramic Flat (WD) Package**

SN54ALVTH16501 . . . WD PACKAGE
SN74ALVTH16501 . . . DGG, DGV, OR DL PACKAGE
(TOP VIEW)



PRODUCT PREVIEW

description

The ’ALVTH16501 devices are 18-bit universal bus transceivers designed for 2.5-V or 3.3-V V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

Data flow in each direction is controlled by output-enable (OEAB and $\overline{\text{OEBA}}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the devices operate in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the low-to-high transition of CLKAB. When OEAB is high, the B-port outputs are active. When OEAB is low, the B-port outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B but uses $\overline{\text{OEBA}}$, LEBA, and CLKBA. The output enables are complementary (OEAB is active high and $\overline{\text{OEBA}}$ is active low).

description (continued)

When V_{CC} is between 0 and 1.2 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.2 V, $\overline{OEBA}$ should be tied to V_{CC} through a pullup resistor and OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN54ALVTH16501 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ALVTH16501 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
OEAB	LEAB	CLKAB	A	B
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	=	L	L
H	L	↑	H	H
H	L	H	X	B_0‡
H	L	L	X	B_0§

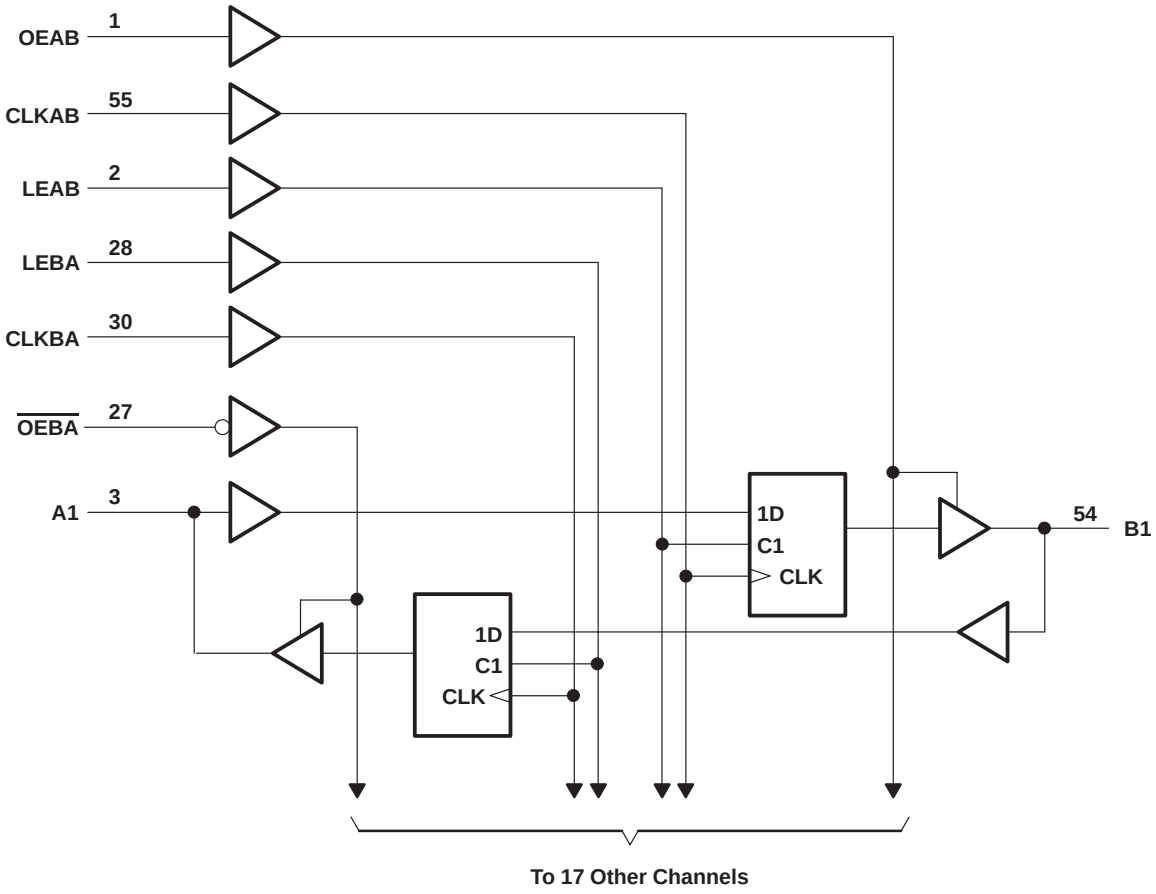
† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, and CLKBA.

‡ Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low

§ Output level before the indicated steady-state input conditions were established

PRODUCT PREVIEW

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O (see Note 1) . . . . . –0.5 V to 7 V
Output current in the low state, I_O: SN54ALVTH16501 . . . . . 96 mA
SN74ALVTH16501 . . . . . 128 mA
Output current in the high state, I_O: SN54ALVTH16501 . . . . . –48 mA
SN74ALVTH16501 . . . . . –64 mA
Input clamp current, I_{IK} ($V_I < 0$) . . . . . –50 mA
Output clamp current, I_{OK} ($V_O < 0$) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 2): DGG package . . . . . 81°C/W
DGV package . . . . . 86°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51.

PRODUCT PREVIEW

recommended operating conditions, V_{CC} = 2.5 V ± 0.2 V (see Note 3)

			SN54ALVTH16501			SN74ALVTH16501			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{CC}	Supply voltage		2.3		2.7	2.3		2.7	V
V_{IH}	High-level input voltage		1.7			1.7			V
V_{IL}	Low-level input voltage				0.7			0.7	V
V_I	Input voltage		0	V_{CC}	5.5	0	V_{CC}	5.5	V
I_{OH}	High-level output current				–6			–8	mA
I_{OL}	Low-level output current				6			8	mA
	Low-level output current; current duty cycle ≤ 50%; f ≥ 1 kHz				18			24	
Δt/Δv	Input transition rise or fall rate	Outputs enabled			10			10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200			200			µs/V
T_A	Operating free-air temperature		–55		125	–40		85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

recommended operating conditions, V_{CC} = 3.3 V ± 0.3 V (see Note 3)

			SN54ALVTH16501			SN74ALVTH16501			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{CC}	Supply voltage		3		3.6	3		3.6	V
V_{IH}	High-level input voltage		2			2			V
V_{IL}	Low-level input voltage				0.8			0.8	V
V_I	Input voltage		0	V_{CC}	5.5	0	V_{CC}	5.5	V
I_{OH}	High-level output current				–24			–32	mA
I_{OL}	Low-level output current				24			32	mA
	Low-level output current; current duty cycle ≤ 50%; f ≥ 1 kHz				48			64	
Δt/Δv	Input transition rise or fall rate	Outputs enabled			10			10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200			200			µs/V
T_A	Operating free-air temperature		–55		125	–40		85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54ALVTH16501			SN74ALVTH16501			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 2.3 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 2.3 V to 2.7 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 2.3 V	I_{OH} = –6 mA	1.8						
			I_{OH} = –8 mA				1.8			
V_{OL}		V_{CC} = 2.3 V to 2.7 V,	I_{OL} = 100 µA			0.2			0.2	V
		V_{CC} = 2.3 V	I_{OL} = 6 mA			0.4				
			I_{OL} = 8 mA						0.4	
			I_{OL} = 18 mA			0.5				
			I_{OL} = 24 mA						0.5	
V_{RST}‡		V_{CC} = 2.7 V	I_O = 1 mA, V_I = V_{CC} or GND			0.55			0.55	V
I_I	Control inputs	V_{CC} = 2.7 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 2.7 V,	V_I = 5.5 V			10			10	
	A or B ports	V_{CC} = 2.7 V	V_I = 5.5 V			10			10	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
I_{BHL}§		V_{CC} = 2.3 V,	V_I = 0.7 V		115			115		µA
I_{BHH}¶		V_{CC} = 2.3 V,	V_I = 1.7 V		–10			–10		µA
I_{BHLO}#		V_{CC} = 2.7 V,	V_I = 0 to V_{CC}	300			300			µA
I_{BHHO}‖		V_{CC} = 2.7 V,	V_I = 0 to V_{CC}	–300			–300			µA
I_{EX}☆		V_{CC} = 2.3 V,	V_O = 5.5 V			125			125	µA
$I_{OZ(PU/PD)}$□		V_{CC} ≤ 1.2 V, V_O = 0.5 V to V_{CC}, V_I = GND or V_{CC}, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 2.7 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.04	0.1		0.04	0.1	mA
			Outputs low		2.5	4.5		2.5	4.5	
			Outputs disabled		0.04	0.1		0.04	0.1	
C_i		V_{CC} = 2.5 V,	V_I = 2.5 V or 0							pF
C_{io}		V_{CC} = 2.5 V,	V_O = 2.5 V or 0							pF

† All typical values are at V_{CC} = 2.5 V, T_A = 25°C.
‡ Data must not be loaded into the flip-flops/latches after applying power.
§ The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL} max.
¶ The bus-hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to V_{IH} min.
# An external driver must source at least I_{BHLO} to switch this node from low to high.
‖ An external driver must sink at least I_{BHHO} to switch this node from high to low.
☆ Current into an output in the high state when V_O > V_{CC}
□ High-impedance state during power up or power down

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		SN54ALVTH16501			SN74ALVTH16501			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}		V_{CC} = 3 V,	I_I = –18 mA			–1.2			–1.2	V
V_{OH}		V_{CC} = 3 V to 3.6 V,	I_{OH} = –100 µA	V_{CC}–0.2			V_{CC}–0.2			V
		V_{CC} = 3 V	I_{OH} = –24 mA	2						
			I_{OH} = –32 mA				2			
V_{OL}		V_{CC} = 3 V to 3.6 V,	I_{OL} = 100 µA			0.2			0.2	V
		V_{CC} = 3 V	I_{OL} = 16 mA						0.4	
			I_{OL} = 24 mA			0.5				
			I_{OL} = 32 mA						0.5	
			I_{OL} = 48 mA			0.55				
			I_{OL} = 64 mA						0.55	
V_{RST}‡		V_{CC} = 3.6 V	I_O = 1 mA, V_I = V_{CC} or GND			0.55			0.55	V
I_I	Control inputs	V_{CC} = 3.6 V,	V_I = V_{CC} or GND			±1			±1	µA
		V_{CC} = 0 or 3.6 V,	V_I = 5.5 V			10			10	
	A or B ports	V_{CC} = 3.6 V	V_I = 5.5 V			10			10	
			V_I = V_{CC}			1			1	
			V_I = 0			–5			–5	
I_{off}		V_{CC} = 0,	V_I or V_O = 0 to 4.5 V						±100	µA
I_{BHL}§		V_{CC} = 3 V,	V_I = 0.8 V	75			75			µA
I_{BHH}¶		V_{CC} = 3 V,	V_I = 2 V	–75			–75			µA
I_{BHLO}#		V_{CC} = 3.6 V,	V_I = 0 to V_{CC}	500			500			µA
I_{BHHO}‖		V_{CC} = 3.6 V,	V_I = 0 to V_{CC}	–500			–500			µA
I_{EX}☆		V_{CC} = 3 V,	V_O = 5.5 V			125			125	µA
$I_{OZ(PU/PD)}$□		V_{CC} ≤ 1.2 V, V_O = 0.5 V to V_{CC}, V_I = GND or V_{CC}, $\overline{OE}$ = don't care				±100			±100	µA
I_{CC}		V_{CC} = 3.6 V, I_O = 0, V_I = V_{CC} or GND	Outputs high		0.06	0.1		0.06	0.1	mA
			Outputs low		3.5	5		3.5	5	
			Outputs disabled		0.06	0.1		0.06	0.1	
ΔI_{CC}◊		V_{CC} = 3 V to 3.6 V, One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND				0.4			0.4	mA
C_i		V_{CC} = 3.3 V,	V_I = 3.3 V or 0							pF
C_{io}		V_{CC} = 3.3 V,	V_O = 3.3 V or 0							pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ Data must not be loaded into the flip-flops/latches after applying power.
§ The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL} max.
¶ The bus-hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to V_{IH} min.
# An external driver must source at least I_{BHLO} to switch this node from low to high.
‖ An external driver must sink at least I_{BHHO} to switch this node from high to low.
☆ Current into an output in the high state when V_O > V_{CC}
□ High-impedance state during power up or power down
◊ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

				SN54ALVTH16501		SN74ALVTH16501		UNIT
				MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency							MHz
t_w	Pulse duration	LE high						ns
		CLK high or low						
t_{su}	Setup time	A or B before CLK↑	Data high					ns
			Data low					
		A or B before LE↓	CLK high					
			CLK low					
t_h	Hold time	A or B after CLK↑	Data high					ns
			Data low					
		A or B after LE↓	CLK high					
			CLK low					

timing requirements over recommended operating free-air temperature range, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 2)

				SN54ALVTH16501		SN74ALVTH16501		UNIT
				MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency							MHz
t_w	Pulse duration	LE high						ns
		CLK high or low						
t_{su}	Setup time	A or B before CLK↑	Data high					ns
			Data low					
		A or B before LE↓	CLK high					
			CLK low					
t_h	Hold time	A or B after CLK↑	Data high					ns
			Data low					
		A or B after LE↓	CLK high					
			CLK low					

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switching characteristics over recommended operating free-air temperature range, C_L = 30 pF, V_{CC} = 2.5 V ± 0.2 V (unless otherwise noted) (see Figure 1)

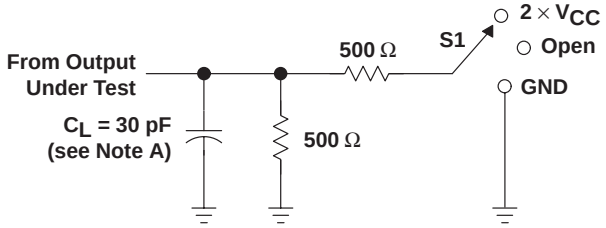
PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ALVTH16501		SN74ALVTH16501		UNIT
			MIN	MAX	MIN	MAX	
f_{max}							MHz
t_{PLH}	B or A	A or B					ns
t_{PHL}							
t_{PLH}	LEBA or LEAB	A or B					ns
t_{PHL}							
t_{PLH}	CLKBA or CLKAB	A or B					ns
t_{PHL}							
t_{PZH}	$\overline{OEBA}$ or OEAB	A or B					ns
t_{PZL}							
t_{PHZ}	$\overline{OEBA}$ or OEAB	A or B					ns
t_{PLZ}							

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF, V_{CC} = 3.3 V ± 0.3 V (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54ALVTH16501		SN74ALVTH16501		UNIT
			MIN	MAX	MIN	MAX	
f_{max}							MHz
t_{PLH}	B or A	A or B					ns
t_{PHL}							
t_{PLH}	LEBA or LEAB	A or B					ns
t_{PHL}							
t_{PLH}	CLKBA or CLKAB	A or B					ns
t_{PHL}							
t_{PZH}	$\overline{OEBA}$ or OEAB	A or B					ns
t_{PZL}							
t_{PHZ}	$\overline{OEBA}$ or OEAB	A or B					ns
t_{PLZ}							

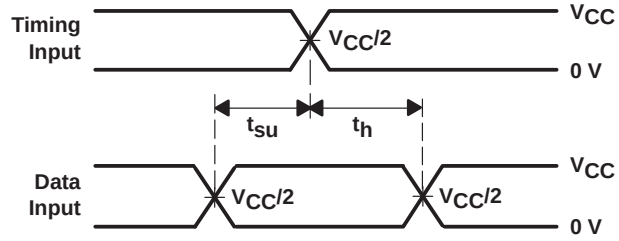
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

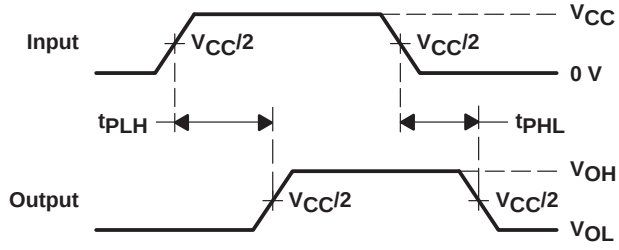


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND

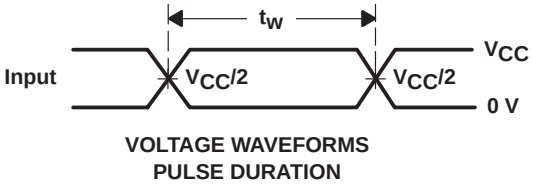
LOAD CIRCUIT



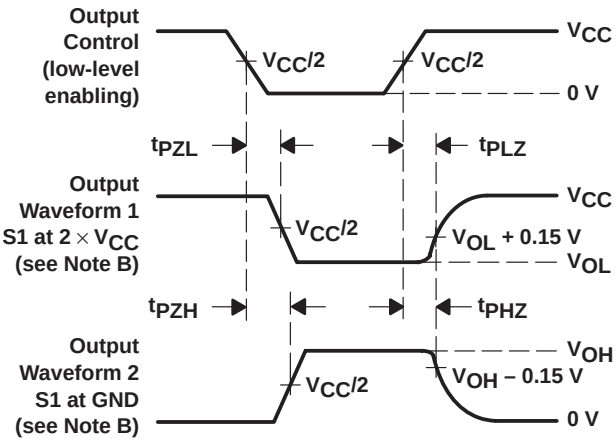
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



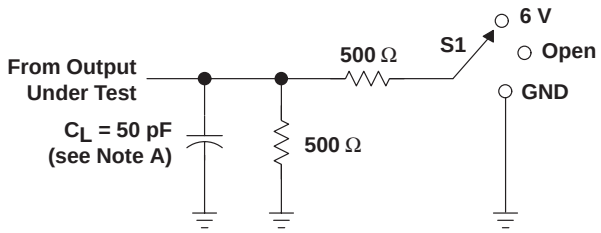
VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

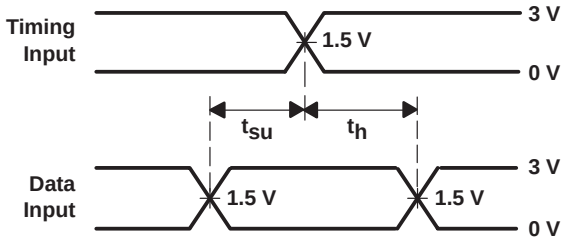
PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 3.3 V ± 0.3 V

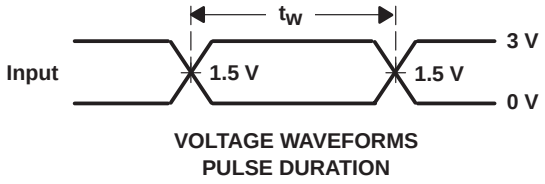


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

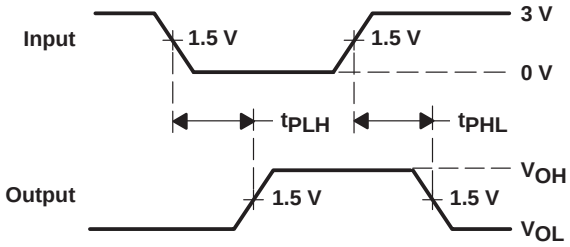
LOAD CIRCUIT



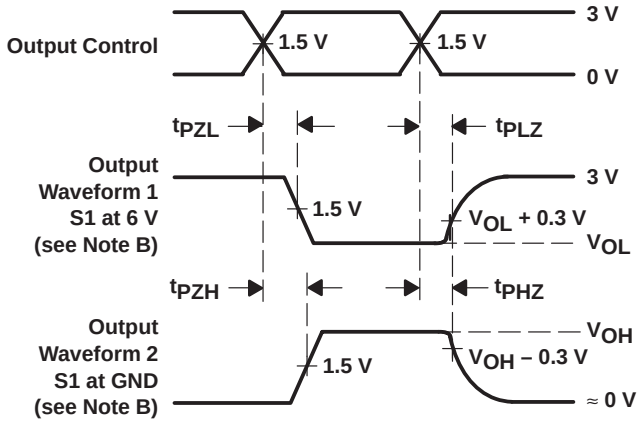
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms

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